

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SD2531

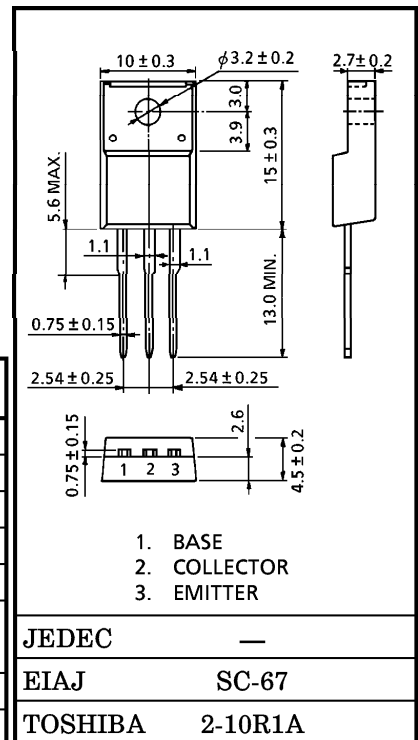
POWER AMPLIFIER APPLICATIONS

Unit in mm

- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.5V$ (Typ.) ($I_C = 2.5A$, $I_B = 0.25A$)
- High Power Dissipation
: $P_C = 25W$ ($T_c = 25^\circ C$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Voltage		V_{CEO}	60	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current		I_C	4	A
Base Current		I_B	1	A
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	2.0	W
	$T_c = 25^\circ C$		25	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 60V$, $I_E = 0$	—	—	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 7V$, $I_C = 0$	—	—	100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10mA$, $I_E = 0$	60	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5V$, $I_C = 0.5A$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = 5V$, $I_C = 3A$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2.5A$, $I_B = 0.25A$	—	0.5	1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5V$, $I_C = 0.5A$	—	0.75	1.0	V
Transition Frequency	f_T	$V_{CE} = 5V$, $I_C = 0.5A$	—	3	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V$, $I_E = 0$, $f = 1MHz$	—	35	—	pF

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